

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	8	LAMARRE-P-.in. LAMARRE-PHILIP-.in. LAMARRE-PHILIP-A-.in. LAMARRE-P-A-.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 11:22
L3	38	(("4204009") or ("4533624") or ("4645562") or ("4767721") or ("4770739") or ("4784936") or ("4806453") or ("4863827") or ("5091342") or ("5140469") or ("5260172") or ("5221596") or ("5296333") or ("5679608") or ("5728504") or ("5817444") or ("5830624") or ("5889788") or ("6156665")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/05/05 11:26
L4	802327	resist photoresist photo-resist photosensitive photo-sensitive (sensitive near (photo light energy radiation))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:27
L5	31231	4 near2 first	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:27
L6	25186	4 near2 second	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:28
L7	120261	barrier near2 (layer film coating)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:35
L8	314	5 same 6 same 7	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:38
L9	127	5 with 6 with 7	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:37
L10	20	3 and 5 and 6	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 13:01
L11	238217	(intermediate barrier) near2 (layer film coating)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:35

L12	108606	latent near2 image	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:36
L13	18	3 not 10	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:36
L14	240	5 with 6 with 11	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:57
L15	3	12 same 14	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:37
L17	5	5 same 6 same 11 same 12	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 11:38
L18	1	us-6653244-\$.did. and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 12:01
L19	3	cem365is	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 12:34
L27	1478	11 with conventional\$3 with metal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 12:53
L28	46	11 with conventional\$3 with metal\$3 with 4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 12:53
L29	160	4 with conventional\$3 with (pmma azide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 13:02
L31	56	4 near3 conventional\$3 near3 (pmma azide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 13:03
L34	233	semiconductor adj substrate near3 conventional\$3 near3 (silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 13:04

L35	28587	semiconductor adj substrate near3 (silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 13:12
L36	2	31 and 35	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 13:12